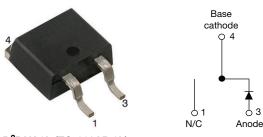


1200 V Gen 3 Power SiC Merged PIN Schottky Diode, 10 A



D²PAK 2L (TO-263AB 2L)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _F	10 A					
V _R	1200 V					
V _F at I _F at 25 °C, typ.	1.35 V					
T _J max.	175 °C					
I _R at V _R at 175 °C	4.5 μA					
Q _C (V _R = 800 V)	55 nC					
Package	D ² PAK 2L (TO-263AB 2L)					
Circuit configuration	Single					

FEATURES

- Minimum creepage and clearance distances are 5.2 mm and 5.4 mm respectively
- Majority carrier diode using Schottky technology on SiC wide band gap material



- High CTI molding compound provides excellent electrical insulation at relevant working voltages
- Improved V_F and efficiency by thin wafer technology
- Positive V temperature coefficient for easy parallelizations.
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 1200 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V_{RRM}		1200	V		
Continuous forward current	I _F ⁽¹⁾	$T_C = 145 ^{\circ}C (DC)$	10	Α		
Continuous forward current	I _F ⁽²⁾	$T_C = 152 ^{\circ}C (DC)$	10	A		
DC blocking voltage	V_{DC}		1200	V		
Repetitive peak forward current	I _{FRM}	T_C = 25 °C, f = 50 Hz, square wave, DC = 25 %	45			
Non-repetitive peak forward surge current	I _{FSM}	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	84	A		
Non-repetitive peak forward surge current		$T_C = 110$ °C, $t_p = 10$ ms, half sine wave	74			
	P _{tot} (1)	$T_C = 25 ^{\circ}C$	94	4 W		
Power dissipation	Ftot ("/	T _C = 110 °C	41	T VV		
rower dissipation	P _{tot} (2)	$T_C = 25 ^{\circ}C$	125	w		
	r _{tot} (=)	T _C = 110 °C	72 VV			
121 -1 -	r.2	$T_C = 25 ^{\circ}C$	61	A 2 -		
I ² t value	∫i ² dt	T _C = 110 °C	27	A ² s		
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C		

Notes

- (1) Based on maximum Rth
- (2) Based on typical R_{th}
- (3) The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta,JA}$



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	OL TEST CONDITIONS		TYP.	MAX.	UNITS	
		I _F = 10 A	-	1.35	1.5		
Forward voltage	V_{F}	I _F = 10 A, T _J = 150 °C	-	1.73	2.0	V	
		I _F = 10 A, T _J = 175 °C	-	1.85	-		
Reverse leakage current	I _R	$V_R = V_R$ rated	-	0.6	60	μA	
		V _R = V _R rated, T _J = 150 °C	-	2.5	130		
		V _R = V _R rated, T _J = 175 °C	-	4.5	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	610	-	pF	
		V _R = 800 V, f = 1 MHz	-	38	-	PΓ	
Total capacitive charge	Q _C	V _R = 800 V, f = 1 MHz	-	55	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS						
Thermal resistance, junction to case	R _{thJC}		-	1.2	1.6	°C/W	
Marking device	3C10ET12S						

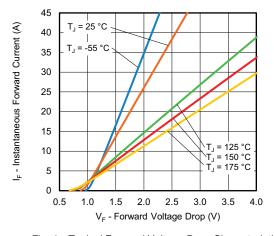


Fig. 1 - Typical Forward Voltage Drop Characteristics

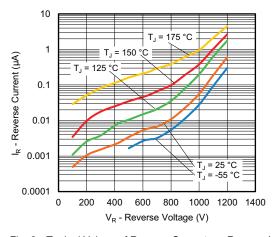


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

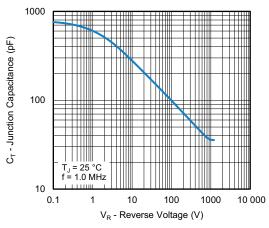


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

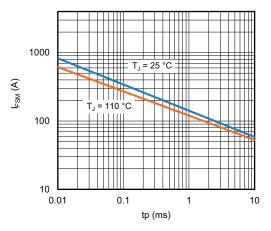


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)



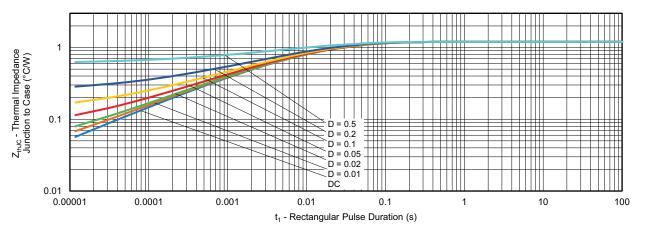


Fig. 5 - Typical Thermal Impedance Z_{thJC} Characteristics

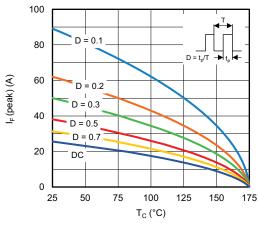


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature

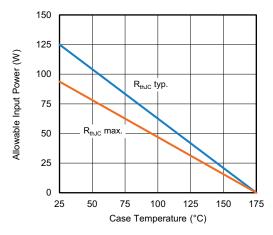


Fig. 7 - Forward Power Loss Characteristics

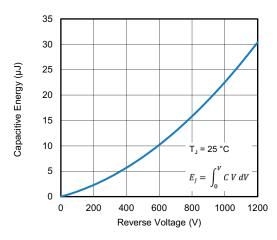


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

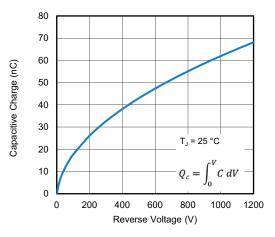
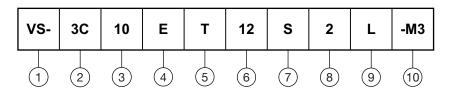


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

- 3C = SiC diode, generation 3

3 - Current rating (10 = 10 A)

4 - E = single diode

T = D²PAK package

6 - Voltage rating: (12 = 1200 V)

7 - S = surface mountable

L = tape and reel (left oriented)

10 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

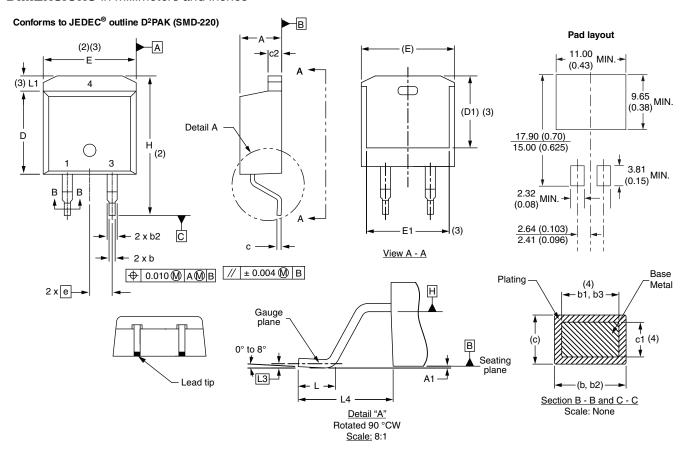
ORDERING INFORMATION					
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-3C10ET12S2L-M3	800 per reel	13" diameter reel			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96683			
Part marking information	www.vishay.com/doc?96693			
Packaging information	www.vishay.com/doc?95032			



D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS		INC	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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